

3875081 G E SOLID STATE

01E 17377 D T-33-19
General-Purpose Power Transistors

File Number 1150

2N4898, 2N4899, 2N4900

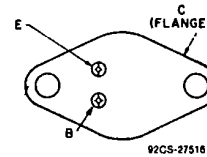
Silicon P-N-P Medium-Power Transistors

General-Purpose Types for Switching Applications

Features:

- Low saturation voltages
- Maximum safe-area-of-operation curves

TERMINAL DESIGNATIONS



JEDEC TO-213AA

The RCA-2N4898, 2N4899 and 2N4900 are multiple-epitaxial p-n-p transistors. All are supplied in the JEDEC TO-213AA package.

All these transistors are intended for a wide variety of medium-power switching and amplifier applications, such as series regulators and output stages of high-fidelity amplifiers.

MAXIMUM RATINGS, Absolute-Maximum Values:

| | 2N4898 | 2N4899 | 2N4900 | |
|--|-----------------|--------|--------|----|
| • V_{CE0} | 40 | 60 | 80 | V |
| • $V_{CEX(SUS)}$ $V_{BE} = -1.5 V, R_{BE} = 100 \Omega$ | 40 | 60 | 80 | V |
| • $V_{CE0(SUS)}$ | 40 | 60 | 80 | V |
| • V_{EBO} | 5 | 5 | 5 | V |
| • I_C | 1 | 1 | 1 | A |
| • I_{CM} | 4 | 4 | 4 | A |
| • I_E | 1 | 1 | 1 | A |
| • P_T At T_C up to 25°C | 25 | 25 | 25 | W |
| At T_C above 25°C | See Figs. 1 & 3 | | | |
| • T_J, T_{stg} | -65 to +200 | | | °C |
| • T_L At distances $\geq 1/32$ in. (0.8 mm) from seating plane for 10 s max. | | +235 | | °C |

* In accordance with JEDEC registration data.

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ELECTRICAL CHARACTERISTICS, At Case Temperature (T_C) = 25°C unless otherwise specified

| CHARACTERISTICS | TEST CONDITIONS | | | | LIMITS | | | | | | UNITS |
|---|---|----------------------|---|----------------|----------------|---------------|----------------|---------------|----------------|---------------|-------|
| | VOLTAGE V dc | | CURRENT A dc | | 2N4898 | | 2N4899 | | 2N4900 | | |
| | V _{CE} | V _{BE} | I _C | I _B | Min. | Max. | Min. | Max. | Min. | Max. | |
| * I _{CBO} | 40 ^a 60 ^a 80 ^a | | | | - | 100 | - | - | - | - | μA |
| * I _{CEX} R _{BE} = 100 Ω | 40 60 80 | -1.5 -1.5 -1.5 | | | - | 100 | - | - | - | - | μA |
| * R _{BE} = 100 Ω T _C = 150°C | 40 60 80 | -1.5 -1.5 -1.5 | | | - | 1 | - | - | - | - | mA |
| * I _{CEO} | 20 30 40 | | | | - | 0.5 | - | - | 0.5 | - | mA |
| * I _{EBO} | | -5 | | | - | 1 | - | 1 | - | 1 | mA |
| * h _{FE} | 1 1 1 | | 0.5 ^b 0.05 ^b 1 ^b | | 20 40 10 | 100 - - | 20 40 10 | 100 - - | 20 40 10 | 100 - - | |
| * V _{CEO(sus)} ^c | | | 0.1 ^b | | 40 | - | 60 | - | 80 | - | V |
| V _{BE(sat)} | | | 1 ^b | 0.1 | - | 1.3 | - | 1.3 | - | 1.3 | V |
| * V _{BE} | 1 | | 1 ^b | | - | 1.3 | - | 1.3 | - | 1.3 | V |
| * V _{CE(sat)} | | | 1 ^b | 0.1 | - | 0.6 | - | 0.6 | - | 0.6 | V |
| * h _{fe} f = 1 kHz | 10 | | 0.25 | | 25 | - | 25 | - | 25 | - | |
| * f _T f = 1 MHz | 10 | | 0.25 | | 3 | - | 3 | - | 3 | - | MHz |
| C _{obo} | 10 ^a | | | | - | 100 | - | 100 | - | 100 | pF |
| R _{θJC} | | | | | - | 7 | - | 7 | - | 7 | °C/W |

* In accordance with JEDEC registration data.

^a V_{CB} value.

^b Pulsed, pulse duration = 300 μs, duty factor = 1.8%.

^c CAUTION: Sustaining voltage, V_{CEO(sus)}, MUST NOT be measured on a curve tracer. (See Figs. 2 and 4.)

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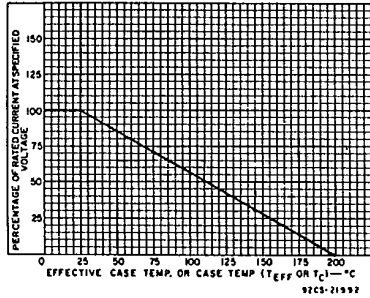


Fig. 1 - Current derating chart for all types.

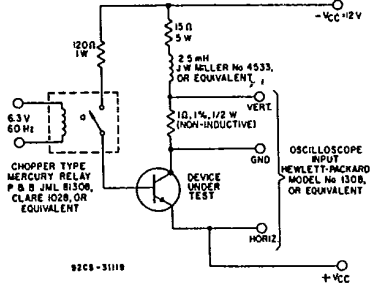


Fig. 2 - Circuit used to measure sustaining voltage, $V_{CE0(sus)}$.

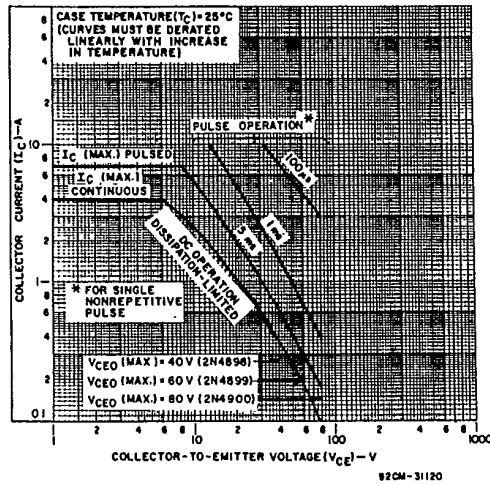
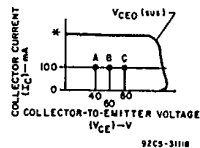


Fig. 3 - Maximum operating areas for all types. ($T_C = 25^\circ C$).

* PULSE CURRENT (I_p) RANGE MUST BE 0.2-0.4A



The sustaining voltage, $V_{CE0(sus)}$, is acceptable when the trace falls to the right of point "A" for type 2N4898; point "B" for type 2N4899; and point "C" for type 2N4900.

Fig. 4 - Oscilloscope display for measurement of sustaining voltages.